

REMARKS

Applicants hereby elect with traverse the prosecution of Group I, method claims 1-29. Non-elected claims 30-41 have been withdrawn from further consideration by the Examiner. The restriction requirement is respectfully traversed for the following reasons. While the Examiner contended that "in the instant case, the product can be made by another and materially different process such as a process without planarizing the copper layer to form a metal interconnect structure and plasma treating the second seed layer with a second treatment plasma prior to the step of forming the copper layer". The Applicants respectfully submit that such are not possible. For the formation of other device features on top of the metal interconnect structure, the electroplated copper layer must be planarized prior to any other deposition steps for forming other device features.

Moreover, the plasma treatment step of the first seed layer cannot be substituted by the plasma treatment of the second seed layer as proposed by the Examiner. Since the plasma treatment step for the first layer is used to (specification, page 12, paragraph 0025) reduce or remove any oxides formed on the seed layer and therefore, forming a substantially oxide-free

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seed layer structure, prior to the deposition of the second seed layer.

The restriction requirement is therefore respectfully traversed. The examination of Group I, claims 1-29, together with the examination of Group II claims 30-41, is respectfully requested of the Examiner.

Respectfully submitted,

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